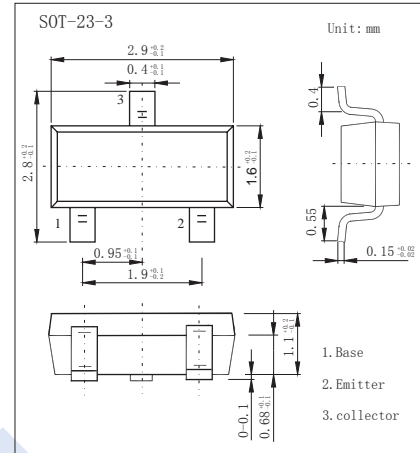


NPN Transistors

2KC1102



■ Features

- Low noise and high gain.

NF = 1.1 dB Typ., $G_a = 11$ dB Typ. @ $V_{CE} = 10$ V, $I_C = 7$ mA, $f = 1.0$ GHz

- High power gain.

MAG = 13 dB Typ. @ $V_{CE} = 10$ V, $I_C = 20$ mA, $f = 1.0$ GHz

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	3.0	V
Collector current (DC)	I_C	100	mA
Total power dissipation	P_{tot}	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu\text{A}$, $I_E = 0$	20			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 \text{ mA}$, $I_B = 0$	12			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}$, $I_C = 0$	3			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 10 \text{ V}$, $I_E = 0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 \text{ V}$, $I_C = 0$			1	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 50 \text{ mA}$, $I_B = 5 \text{ mA}$			0.4	V
Base - emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 50 \text{ mA}$, $I_B = 5 \text{ mA}$			1.2	
DC current gain *	h_{FE}	$V_{CE} = 10 \text{ V}$, $I_C = 20 \text{ mA}$	125		250	
Insertion power gain	$ S_{21e} ^2$	$V_{CE} = 10 \text{ V}$, $I_C = 20 \text{ mA}$, $f = 1 \text{ GHz}$		11.5		dB
Noise figure	NF	$V_{CE} = 10 \text{ V}$, $I_C = 7 \text{ mA}$, $f = 1 \text{ GHz}$		1.1	2	
Reverse transfer capacitance	C_{re}	$V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		0.55	1	pF
Transition frequency	f_T	$V_{CE} = 10 \text{ V}$, $I_C = 20 \text{ mA}$		7		GHz

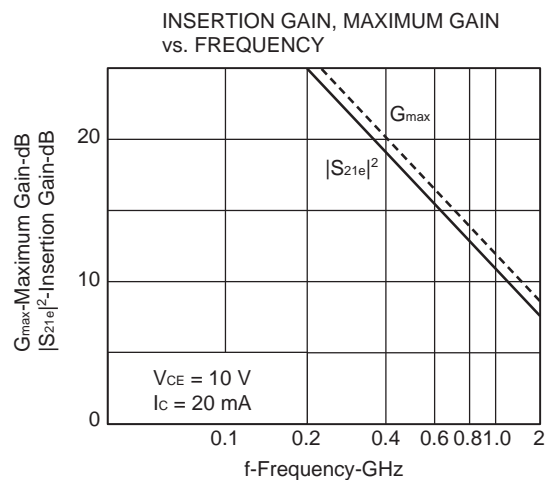
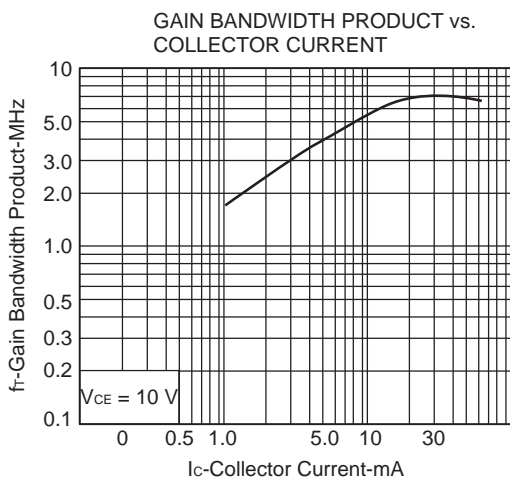
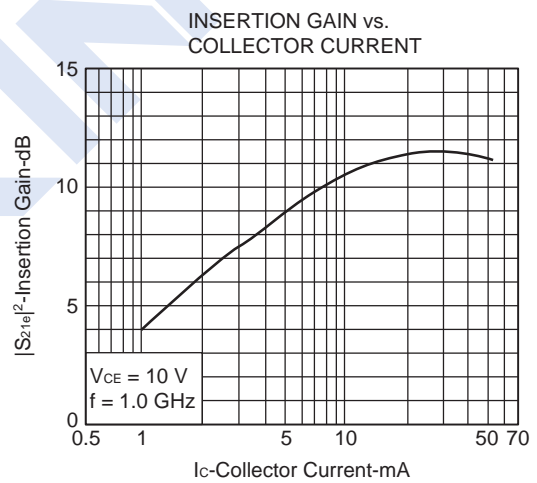
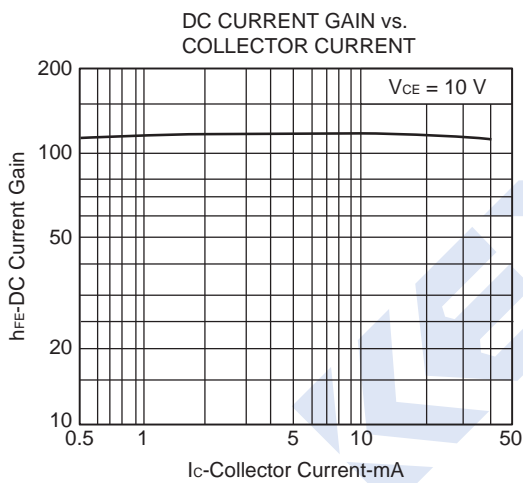
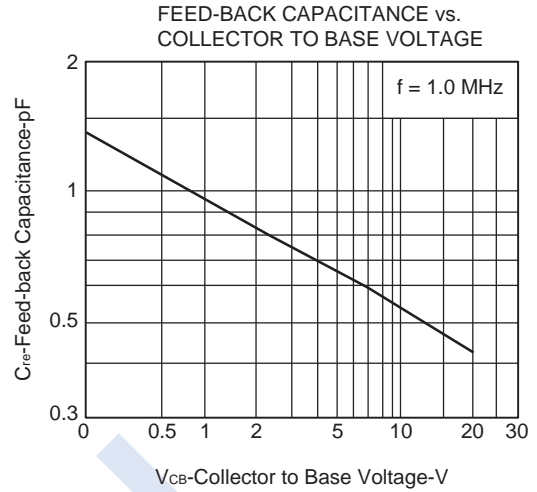
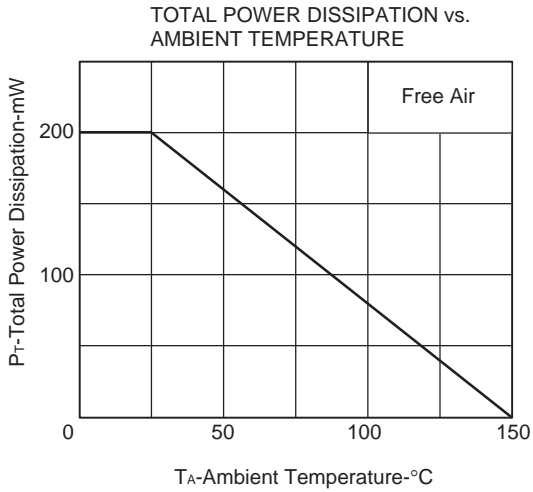
*. Pulse measurement: $PW \leq 350 \mu\text{s}$, Duty Cycle $\leq 2\%$.

■ Marking

Marking	R02
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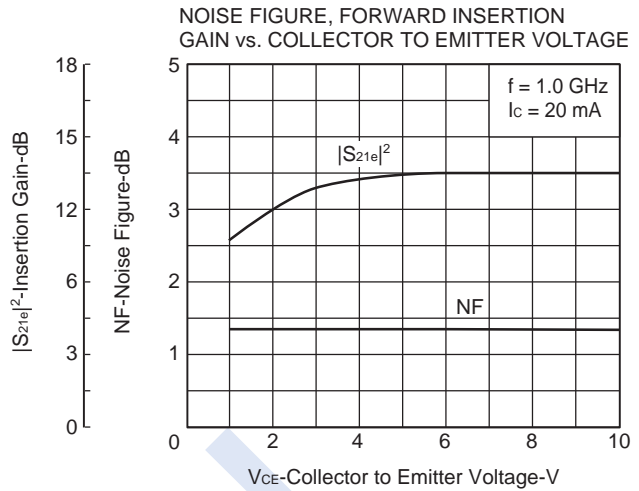
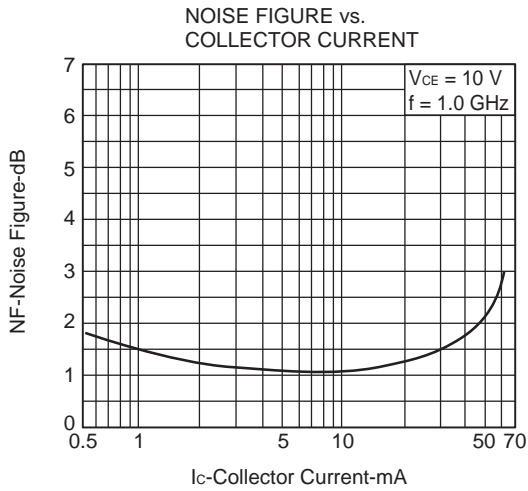
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Typical Characteristics

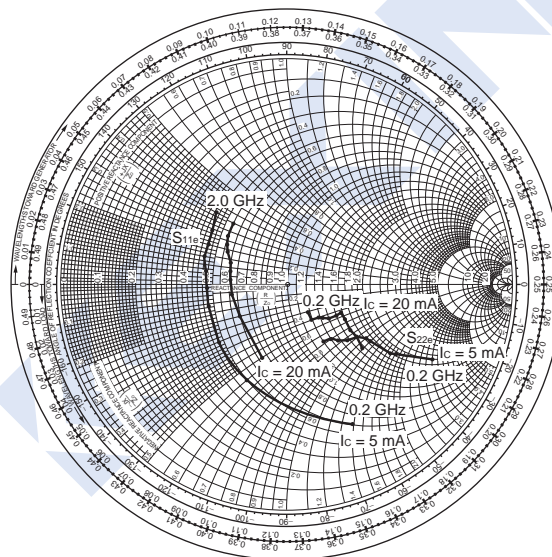


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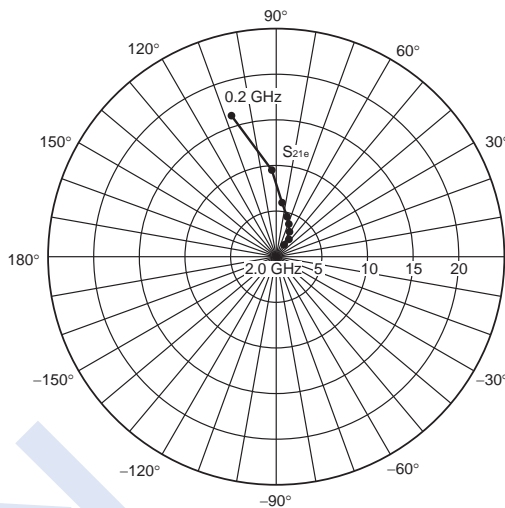
■ Typical Characteristics



S_{11e}, S_{22e}-FREQUENCY
CONDITION $V_{CE} = 10\text{ V}$
200 MHz Step



S_{21e}-FREQUENCY
CONDITION $V_{CE} = 10\text{ V}$
 $I_c = 20\text{ mA}$



S_{12e}-FREQUENCY
CONDITION $V_{CE} = 10\text{ V}$
 $I_c = 20\text{ mA}$

